

### ● General Description

The AGM609MNA combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

This device is ideal for load switch and battery protection applications.

### ● Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

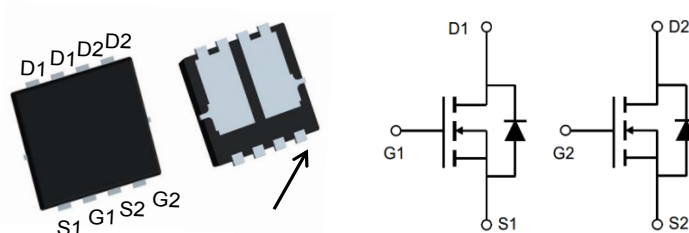
### ● Application

- Electronic Ballast
- Electronic Transformer
- Switch Mode Power Supply

### Product Summary

BVDSS	RDSON	ID
60V	6.5mΩ	70A

### PDFN5\*6 Pin Configuration



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM609MNA	AGM609MNA	PDFN5*6	330mm	12mm	3000

Table 1. Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ )

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage ( $V_{GS}=0V$ )	60	V
VGS	Gate-Source Voltage ( $V_{DS}=0V$ )	$\pm 20$	V
ID	Drain Current-Continuous( $T_c=25^\circ\text{C}$ ) (Note 1)	70	A
	Drain Current-Continuous( $T_c=100^\circ\text{C}$ )	40	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	280	A
PD	Maximum Power Dissipation( $T_c=25^\circ\text{C}$ )	54	w
	Maximum Power Dissipation( $T_c=100^\circ\text{C}$ )	22	w
EAS	Avalanche energy (Note 3)	28	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	50	$^\circ\text{C}/\text{W}$
RθJC	Thermal Resistance Junction-Case <sup>1</sup>	---	2.3	$^\circ\text{C}/\text{W}$

**Table 3. Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.2	1.6	2.1	V
gFS	Forward Transconductance	VDS=5V, ID=15A	--	5	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=20A	--	6.5	9.0	mΩ
		VGS=4.5V, ID=15A	--	9.5	12.5	mΩ
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=30V, VGS=0V, F=1MHZ	--	1456	--	pF
Coss	Output Capacitance		--	424	--	pF
Crss	Reverse Transfer Capacitance		--	14	--	pF
Rg	Gate resistance	VGS=0V,	--	1.3	--	Ω
<b>Switching Times</b>						
td(on)	Turn-on Delay Time	VDD=30V, RD = 5Ω, RG = 10Ω VGS=10V	--	15	--	nS
tr	Turn-on Rise Time		--	20	--	nS
td(off)	Turn-Off Delay Time		--	37	--	nS
tf	Turn-Off Fall Time		--	7	--	nS
Qg	Total Gate Charge	VGS=10V, VDD=30V, ID=20A	--	26.9	--	nC
Qgs	Gate-Source Charge		--	7.2	--	nC
Qgd	Gate-Drain Charge		--	3.5	--	nC
<b>Source-Drain Diode Characteristics</b>						
ISD	Source-Drain Current(Body Diode)		--	--	70	A
VSD	Forward on Voltage	VGS=0V, ISD=10A	--	--	1.2	V
trr	Reverse Recovery Time	VDD=30V, IF=10A , di/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T<sub>J</sub>=25°C

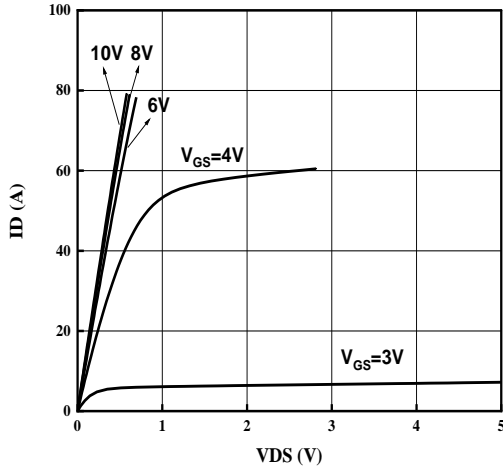


Fig1. Typical Output Characteristics

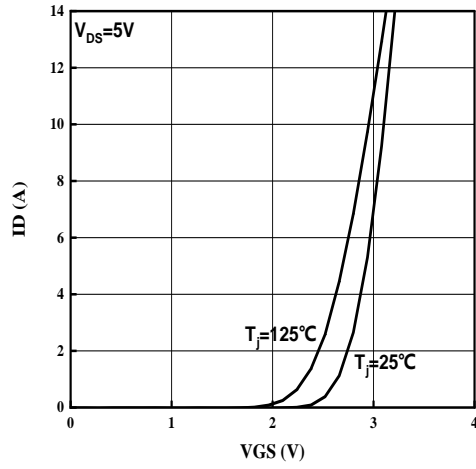


Fig2. Typical Transfer Characteristics

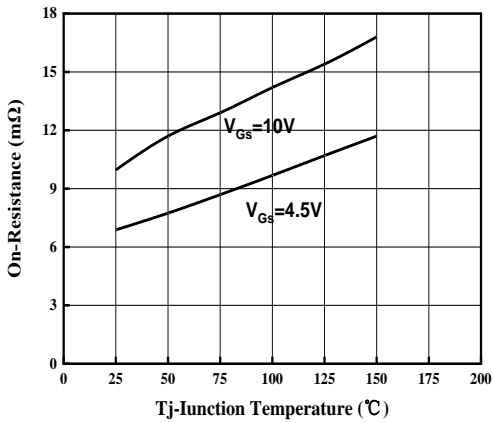


Fig3. Normalized On-Resistance Vs. Temperature

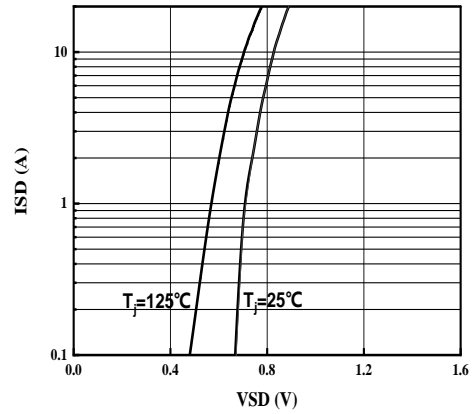


Fig4. Typical Source-Drain Diode Forward Voltage

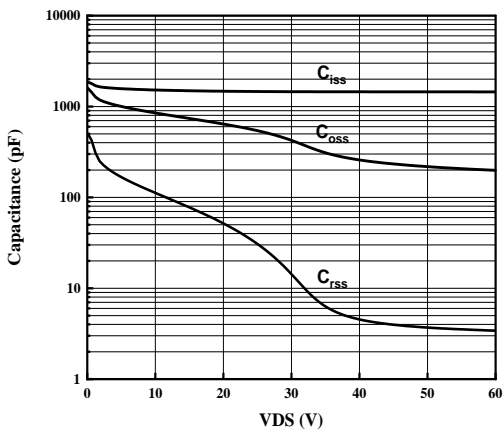


Fig5. Typical Capacitance

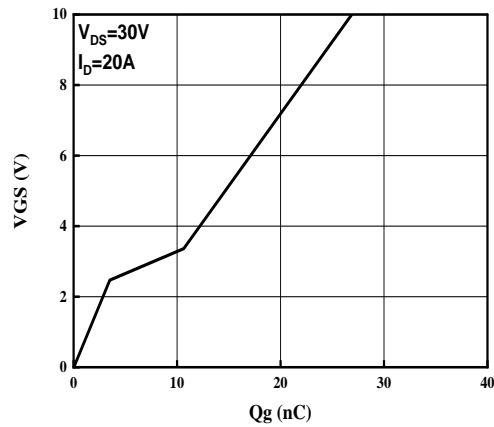


Fig6. Typical Gate Charge

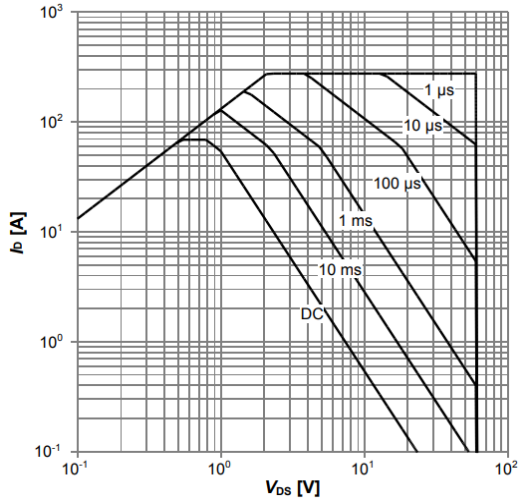


Fig7. Safe Operating Area

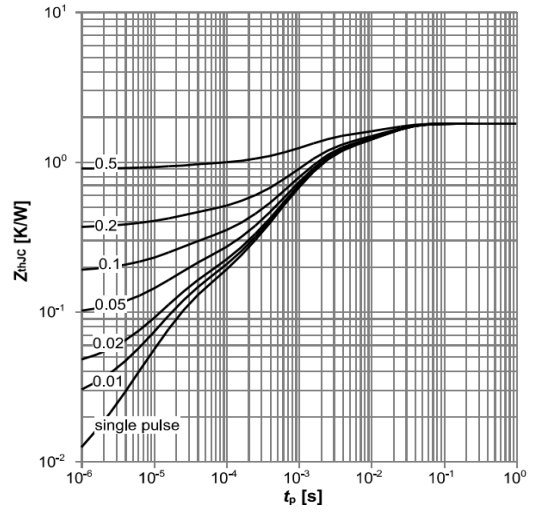
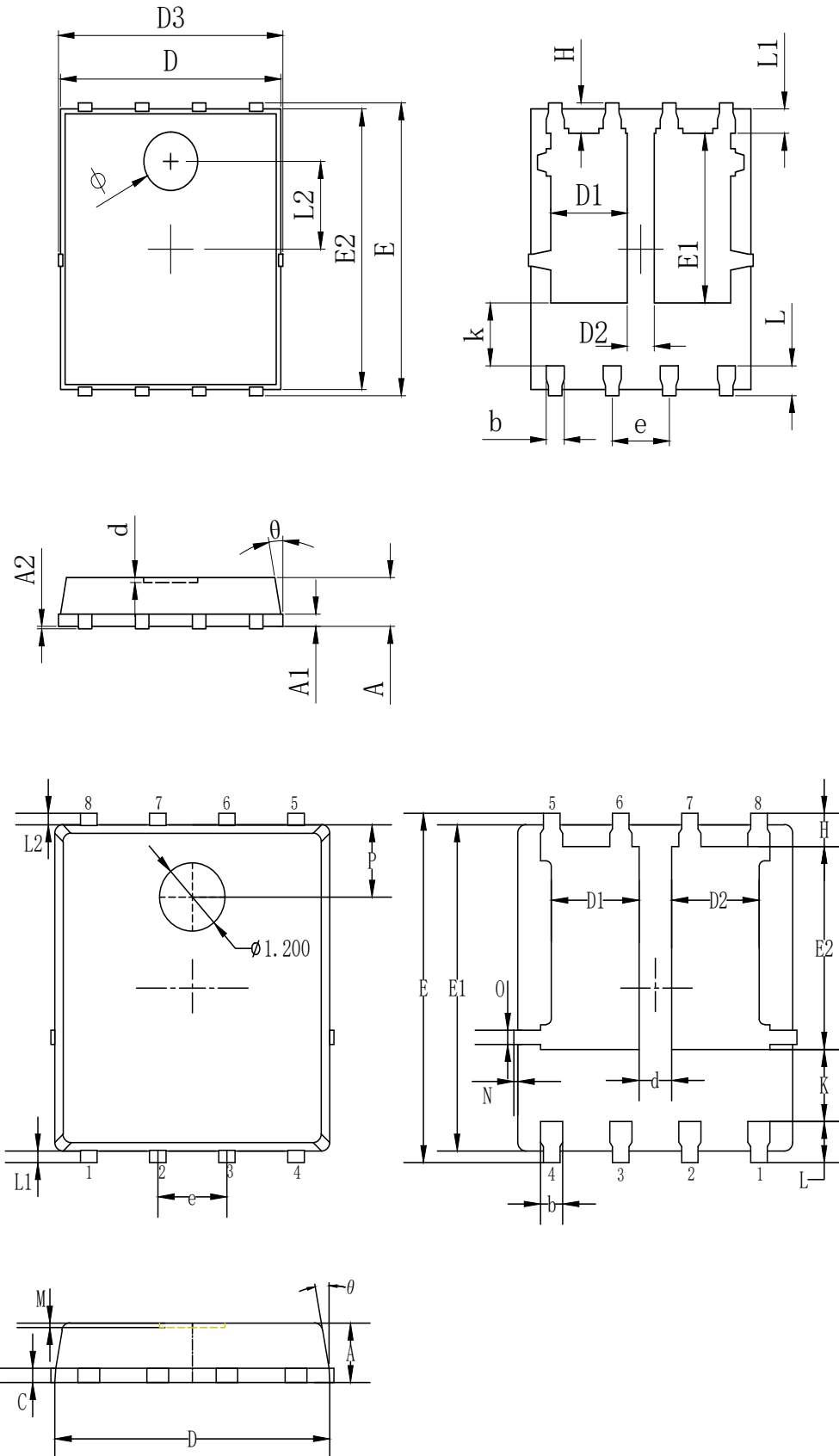


Fig8. Max. transient thermal impedance

**•Dimensions (PDFN5\*6)**


SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0 <sup>~</sup> 0.05		
D	4.824	4.900	4.976
D1	1.605	1.705	1.805
D2	0.500	0.600	0.700
D3	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
$\theta$	8°	10°	12°
$\phi$	1.100	1.200	1.300
d			0.100

Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1/D2	1.51	1.61	1.71
d	0.50	0.60	0.70
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
$\theta$	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		


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